

N-Ch 60V Fast Switching MOSFETs

- ★ Green Device Available
- ★ Super Low Gate Charge
- ★ Excellent CdV/dt effect decline
- ★ Advanced high cell density Trench technology

Product Summary

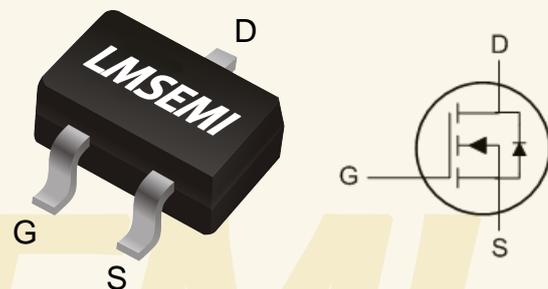
$V_{(BR)DSS}$	$R_{DS(on)}$	ID
60V	75 mΩ	3A

Description

The IRLML0060 is the high cell density trenched N-ch MOSFETs, which provides excellent $R_{DS(ON)}$ and efficiency for most of the small power switching and load switch applications.

The IRLML0060 meet the RoHS and Green Product requirement with full function reliability approved.

SOT-23 Pin Configuration



Absolute Maximum Ratings ($T_A=25^{\circ}C$ unless otherwise specified)

Symbol	Parameter	Max.	Units
V_{DSS}	Drain-Source Voltage	60	V
V_{GSS}	Gate-Source Voltage	±20	V
I_D	Continuous Drain Current	$T_A = 25^{\circ}C$	3
		$T_A = 100^{\circ}C$	2
I_{DM}	Pulsed Drain Current ^{note1}	12	A
P_D	Power Dissipation	$T_A = 25^{\circ}C$	1.5
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	83	$^{\circ}C/W$
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +150	$^{\circ}C$

Electrical Characteristics ($T_J=25^{\circ}\text{C}$ unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	60	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=60V, V_{GS}=0V,$	-	-	1.0	μA
I_{GSS}	Gate to Body Leakage Current	$V_{DS}=0V, V_{GS}=\pm 20V$	-	-	± 100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	1.0	1.4	2.0	V
$R_{DS(on)}$	Static Drain-Source on-Resistance note2	$V_{GS}=10V, I_D=3A$	-	75	90	m Ω
		$V_{GS}=4.5V, I_D=2A$	-	95	120	
Dynamic Characteristics						
C_{iss}	Input Capacitance	$V_{DS}=25V, V_{GS}=0V,$ $f=1.0MHz$	-	350	-	pF
C_{oss}	Output Capacitance		-	29	-	pF
C_{riss}	Reverse Transfer Capacitance		-	23	-	pF
Q_g	Total Gate Charge	$V_{DS}=30V, I_D=3A,$ $V_{GS}=10V$	-	9	-	nC
Q_{gs}	Gate-Source Charge		-	1.5	-	nC
Q_{gd}	Gate-Drain("Miller") Charge		-	2	-	nC
Switching Characteristics						
$t_{d(on)}$	Turn-on Delay Time	$V_{DD}=30V, I_D=2A,$ $R_{GEN}=3\Omega, V_{GS}=10V$	-	5	-	ns
t_r	Turn-on Rise Time		-	7	-	ns
$t_{d(off)}$	Turn-off Delay Time		-	37	-	ns
t_f	Turn-off Fall Time		-	22	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain to Source Diode Forward Current		-	-	3	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	12	A
V_{SD}	Drain to Source Diode Forward Voltage	$V_{GS} = 0V, I_S=3A$	-	-	1.2	V

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 0.5\%$

Typical Performance Characteristics

Figure 1: Output Characteristics

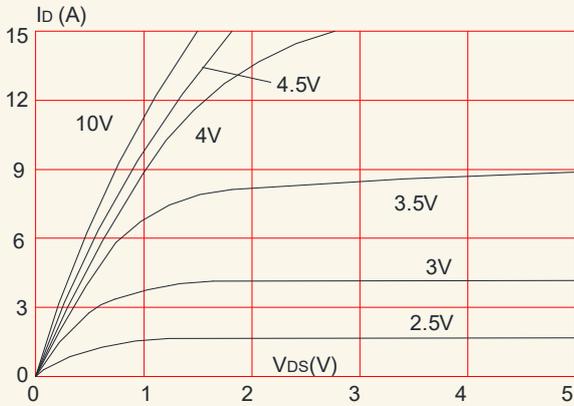


Figure 2: Typical Transfer Characteristics

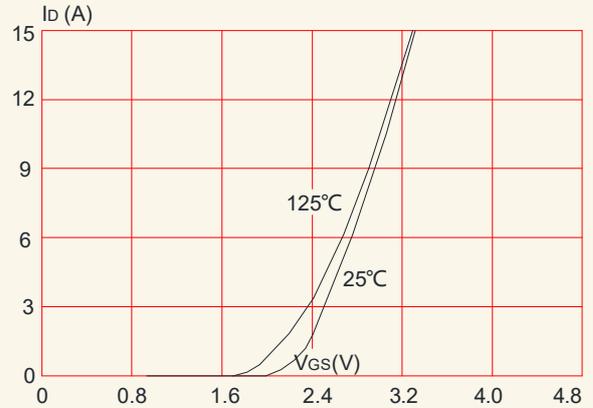


Figure 3: On-resistance vs. Drain Current

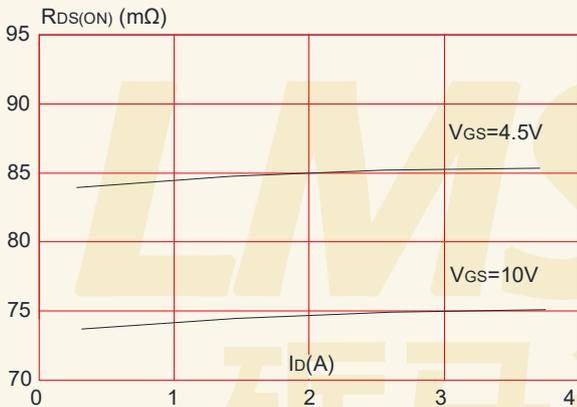


Figure 4: Body Diode Characteristics

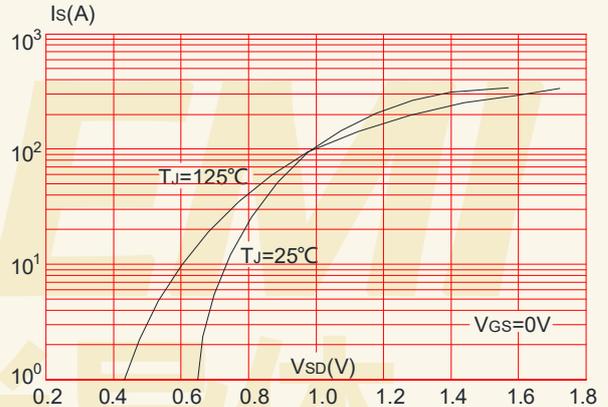


Figure 5: Gate Charge Characteristics

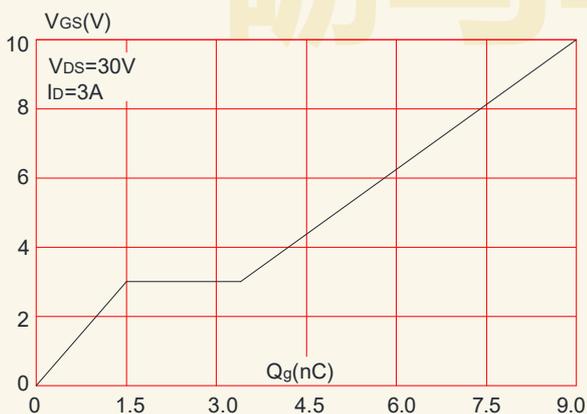


Figure 6: Capacitance Characteristics

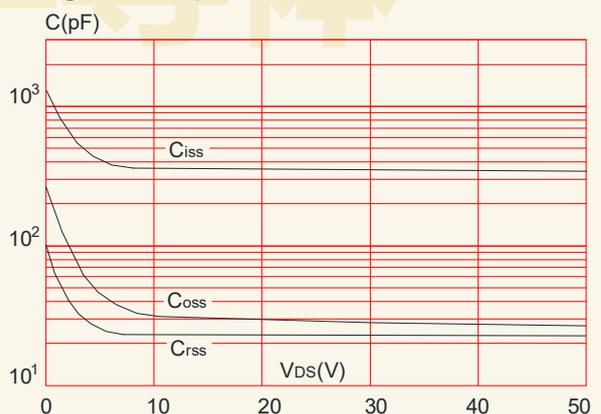


Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

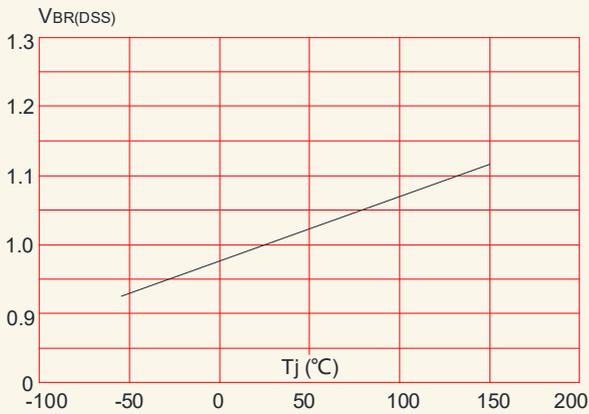


Figure 8: Normalized on Resistance vs. Junction Temperature

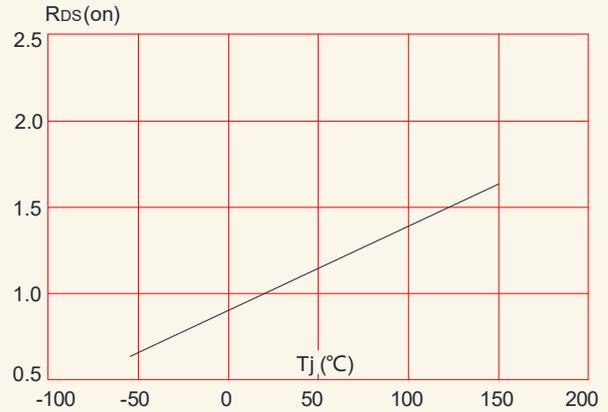


Figure 9: Maximum Safe Operating Area

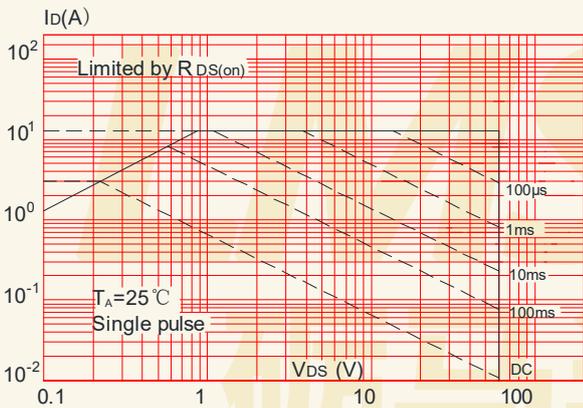


Figure 10: Maximum Continuous Drain Current vs. Ambient Temperature

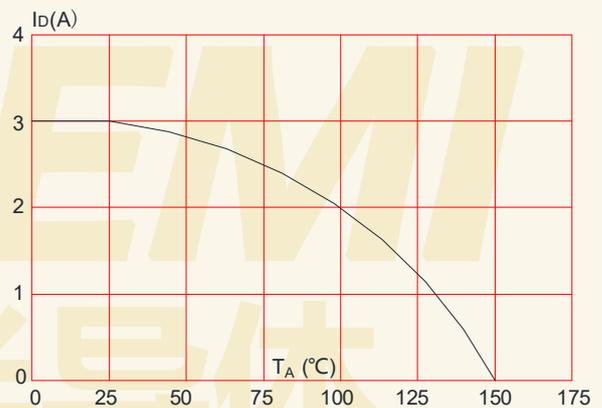
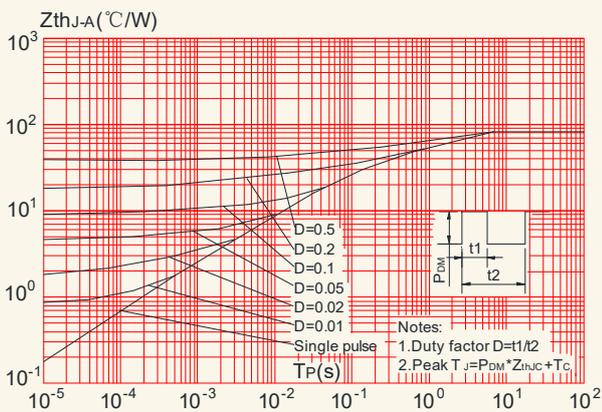
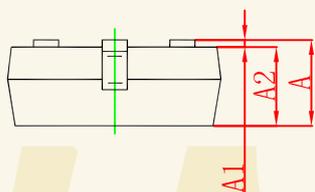
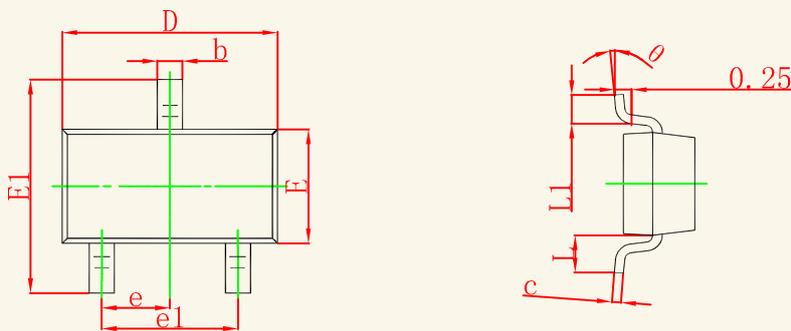


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

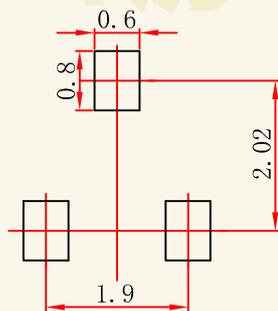


SOT-23 Package Outline Dimensions



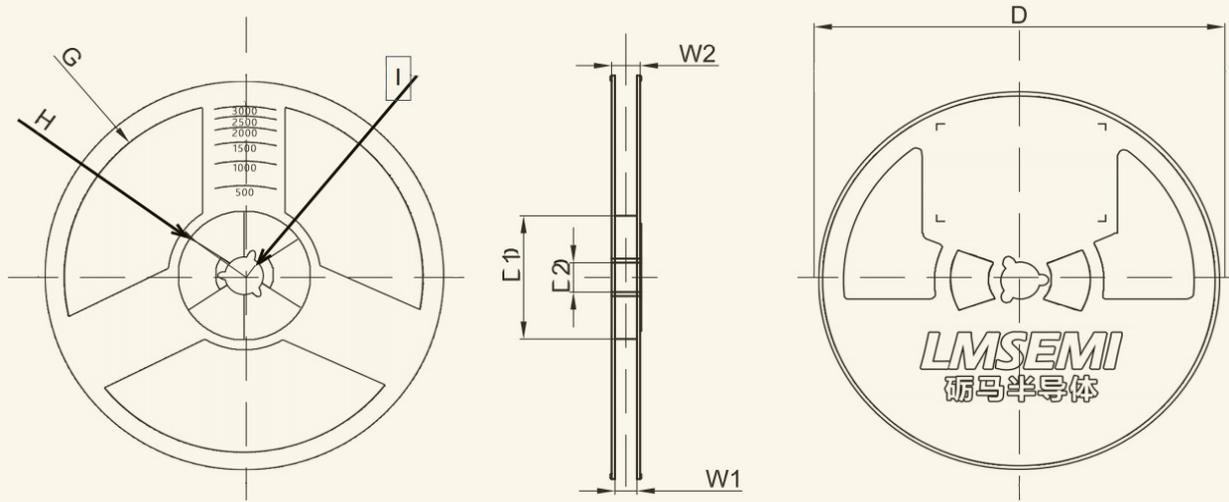
Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP		0.037 TYP	
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022 REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°

SOT-23 Suggested Pad Layout



- Note:
1. Controlling dimension: in millimeters.
 2. General tolerance: $\pm 0.05\text{mm}$.
 3. The pad layout is for reference purposes only.

SOT-23 Reel



Dimensions are in millimeter

Reel Option	D	D1	D2	G	H	I	W1	W2
7" Dia	Ø178.00	54.40	13.00	R78.00	R25.60	R6.50	9.50	12.30

REEL	Reel Size	Box	Box Size(mm)	Carton	Carton Size(mm)	G.W.(kg)
3000 pcs	7 inch	30,000 pcs	183×126×183	180,000 pcs	395×380×200	

砺马半导体

NOTICE

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